

RF Low Noise FET CE7613M4

12G Low Noise FET in Dual mold Plastic PKG

Description :

- Super Low Noise and high Gain
- Original Dual mold Plastic package



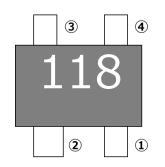
Applications :

• Ku-band LNB (Low Noise Block)

Package :

 Flat-lead 4-pin thin-type super minimold package

PIN Configuration :



| PIN No. | PIN Name | | |
|---------|----------|--|--|
| 1 | Source | | |
| 2 | Drain | | |
| 3 | Source | | |
| 4 | Gate | | |

Ordering Information :

| Part Number | Order Number | Package | Marking | Supplying Form |
|-------------|--------------|-------------------------------------|---------|----------------------------------|
| CE7613M4 | CE7613M4-C2 | Flat-lead 4-pin thin- type super | 118 | •Embossed 8 mm wide |
| | | minimold package ·Pin 1 (S | | •Pin 1 (Source), Pin 2 (Drain) |
| | | | | Face the perforation side of the |
| | | | | Таре |
| | | | | •Qty 15Kpcs/reel |
| | | | | |

Absolute Maximum Ratings :

| Parameter | Symbol | Rating | Unit |
|-------------------------|--------|----------------|------|
| Drain to Source Voltage | VDS | 4.0 | V |
| Gate to Source Voltage | VGS | -2.4 | V |
| Drain Current | ID | IDSS | mA |
| Gate Current | IG | 80 | μA |
| Total Power Dissipation | Ptot | 125 | mW |
| Channel Temperature | Tch | +150 | °C |
| Storage Temperature | Tstg | -55 to +125 °C | |
| Operation temperature | Тор | -55 to +125 | ° |

Recommended Operating Range :

(TA=+25°C, unless otherwise specified)

| Parameter | Symbol | MIN. | TYP. | MAX. | Unit |
|--|--------|------|------|------|------|
| Drain to Source Voltage | VDS | +1 | +2 | +3 | V |
| Drain Current (ID constant circuit) | ID | 5 | 10 | 15 | mA |

Electrical Characteristics :

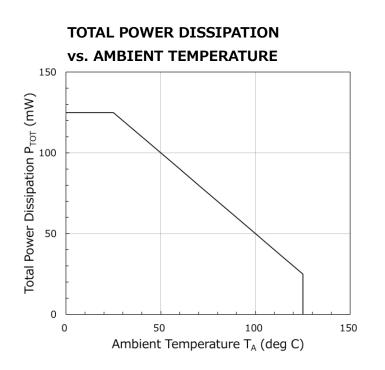
(TA=+25°C, unless otherwise specified)

| Parameter | Symbol | Condition | MIN. | TYP. | MAX. | Unit |
|--------------------------------|----------|------------------|-------|-------|-------|------|
| Gate to Source Leak Current | IGSO | VGS=-3.0V | - | 0.30 | 10.0 | μA |
| Saturated Drain Current | IDSS | VDS=2V, VGS=0V | 6.3 | 20.0 | 31.9 | mA |
| Gate to Source Cut-off Voltage | VGS(off) | VDS=2V, ID=120µA | -0.67 | -0.40 | -0.10 | V |
| Trans conductance | Gm | VDS=2V, ID=10mA | 51.8 | 73.4 | - | mS |
| Noise Figure | NF | VDS=2V, ID=10mA, | - | 0.35 | 0.53 | dB |
| Associated Gain | Ga | f=12GHz | 12.4 | 14.1 | - | dB |

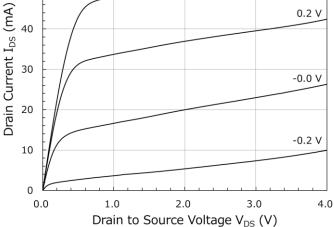
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TYPICAL CHARACTERISTICS :

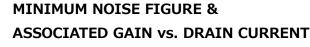
(TA=+25℃, unless otherwise specified)

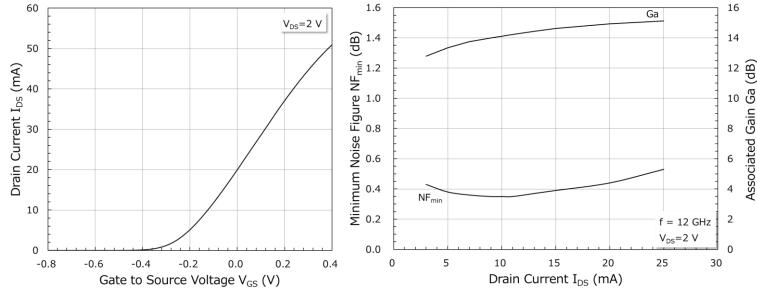


DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



DRAIN CURRENT vs. GATE TO SOURCE VOLTAGE

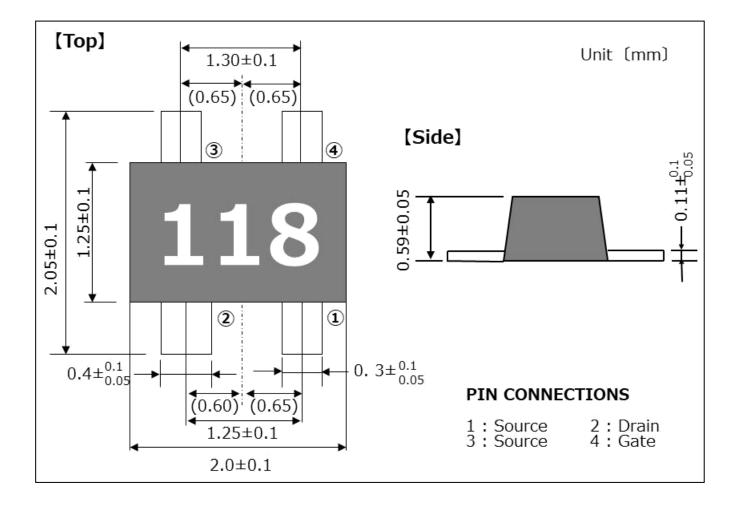




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Package Dimensions :





REVISION HISTORY

| Version | Change to current version | Page(s) |
|---------------------------------|---------------------------|---------|
| CDS-0069-02 November 9, 2020 | Initial datasheet | N/A |
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